

**AMENDMENTS TO THE CLAIMS**

**Claim 1 (Original): A semiconductor acceleration sensor comprising:**

5           a non-single-crystal-silicon-based substrate;  
              an insulating beam structure having a movable section and a stationary section;  
              at least one piezoresistor positioned on the beam structure;  
10          an insulating supporter positioned on the non-single-crystal-silicon-based substrate for fixing the stationary section of the beam structure and forming a distance between the beam structure and the non-single-crystal-silicon-based  
15          substrate; and  
              a thin film transistor (TFT) control circuit positioned on the non-single-crystal-silicon-based substrate and electrically connected to the piezoresistor and the beam structure.  
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**Claim 2 (Original): The semiconductor acceleration sensor of claim 1 wherein the non-single-crystal-silicon-based substrate is a glass substrate.**

**Claim 3 (Original): The semiconductor acceleration sensor of claim 2 wherein the TFT control circuit is a low temperature polysilicon TFT control circuit.**

**30          Claim 4 (Original): The semiconductor acceleration sensor of claim 1 wherein the**

non-single-crystal-silicon-based substrate is a quartz substrate.

Claim 5 (Original): The semiconductor acceleration sensor of claim 4 wherein the TFT control circuit is a high temperature polysilicon TFT control circuit.

Claim 6 (Original): The semiconductor acceleration sensor of claim 1 wherein the beam structure and the supporter are formed simultaneously.

Claim 7 (Original): The semiconductor acceleration sensor of claim 6 wherein the beam structure and the supporter both comprise silicon dioxide.

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Claim 8 (Original): The semiconductor acceleration sensor of claim 1 wherein the piezoresistor comprises doped polysilicon.

20 Claim 9 (Original): The semiconductor acceleration sensor of claim 1 wherein the piezoresistor comprises a piezoelectric thin film.

Claim 10 (Original): The semiconductor acceleration sensor of claim 9 wherein the piezoelectric thin film comprises ZnO, BaTiO<sub>3</sub>, or PbZrTiO<sub>3</sub> (PZT).

30 Claim 11 (Original): The semiconductor acceleration sensor of claim 1 wherein the non-single-crystal-silicon-based substrate further comprises a thin film transistor display region for displaying a variation of pressure detected by the

semiconductor acceleration sensor.

Claims 12-23 (Cancelled)

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